

# TSH10

# 140MHz BANDWIDTH LOW NOISE SINGLE OPERATIONAL AMPLIFIER



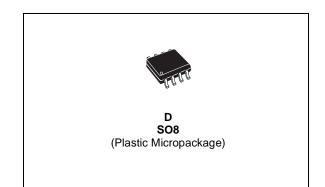
#### DESCRIPTION

The TSH10 is a low cost wide bandwidth single operational amplifier featuring low input noise of  $6nV/\sqrt{Hz}$ . Other features as unity gain stability, fast settling time and high linearity make it suitable for any application requiring speed and precision as high resolution video or DAC buffer.

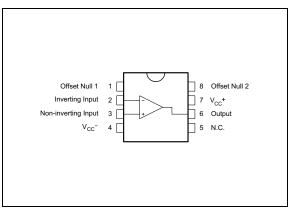
#### **ORDER CODE**

Part Number	Temperature Range	Package
Fait Nulliber	Temperature Range	D
TSH10I	-40°C, +125°C	•

**D** = Small Outline Package (SO) - also available in Tape & Reel (DT)

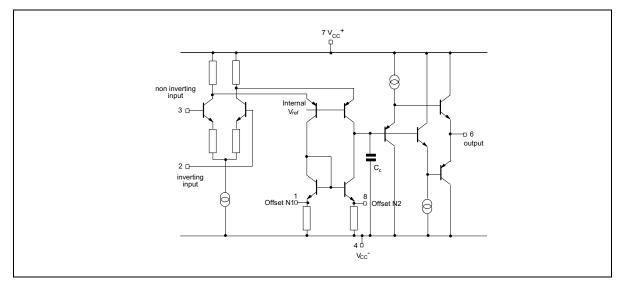


## PIN CONNECTIONS (top view)

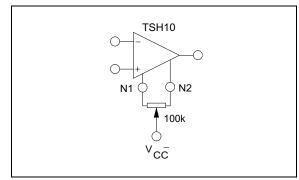


# TSH10

#### SCHEMATIC DIAGRAM



## INPUT OFFSET VOLTAGE NULL CIRCUIT



#### MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	±7	V
V <sub>id</sub>	Differential Input Voltage	±5	V
Vi	Input Voltage	±5	V
l <sub>in</sub>	Current On Inputs Current On Offset Null Pins	±50 ±20	V
T <sub>oper</sub>	Operating Free-Air Temperature range	-40 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C

#### **OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>cc</sub>	Supply Voltage	±3 to ±6	V
V <sub>ic</sub>	Common Mode Input Voltage Range	$V_{CC}^{-}$ +2 to $V_{CC}^{+}$ -1	V

**\\\** 

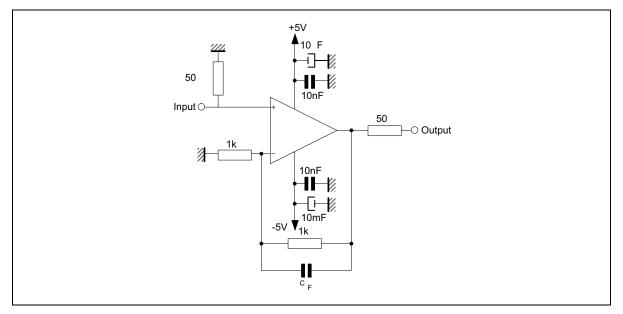
# ELECTRICAL CHARACTERISTICS

 $V_{\text{CC}} = \pm 5 V, \, T_{\text{amb}} = 25^{\circ} C$  (unless otherwise specified)

Symbol	Parameter		Min.	Тур.	Max.	Unit
V <sub>io</sub>	Input Offset Voltage			1	10	mV
DV <sub>io</sub>	Input Offset Voltage Drift $T_{min.} \leq T_{amb} \leq T_{max.}$			20		μV/°C
l <sub>ib</sub>	Input Bias Current			5	30	μA
l <sub>io</sub>	Input Offset Current			0.1	10	μΑ
I <sub>CC</sub>	Supply Current, no load	$V_{CC} = \pm 5V$		20	40	mA
Avd	Large Signal Voltage Gain Vo = ±2.5V	R <sub>L</sub> = 100Ω	200	800		V/V
V <sub>icm</sub>	Input Common Mode Voltage Range		-3 to +4	-3.5 to +4.5		V
CMR	Common-mode Rejection Ratio V <sub>ic</sub> = V <sub>icm min.</sub>		55	100		V
SVR	Supply Voltage Rejection Ratio V <sub>CC</sub> = ±5V to ±3V		45	70		dB
Vo	Output Voltage	$R_L = 100\Omega$	±2.5	+3.5 -3.7		V
I <sub>o</sub>	Output Short Circuit Current Vid = $\pm 1V$ , Vo = 0V			±70		mA
GBP	Gain Bandwidth Product $A_{VCL} = 100, R_L = 100\Omega, f = 7.5M$	IHz		140		MHz
SR	Slew Rate $V_{in} = \pm 2V, A_{VCL} = 1, R_L = 100\Omega$			150		V/µs
e <sub>n</sub>	Equivalent Input Voltage Noise	f = 1MHz		6		nV/ √Hz
φm	Phase Margin $A_{VM} = 1$ , $R_L = 100\Omega$ , $C_L = 15pF$			40		Degrees

## TSH10

#### **EVALUATION CIRCUIT**



#### PRINTED CIRCUIT LAYOUT

As for any high frequency device, a few rules must be observed when designing the PCB to get the best performances from this high speed op amp.

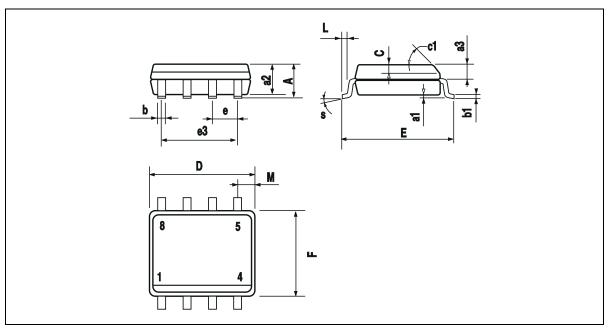
From the most to the least important points :

- Each power supply lead has to be bypassed to ground with a 10nF ceramic capacitor very close to the device and a 10μF tantalum capacitor.
- To provide low inductance and low resistance common return, use a ground plane or common point return for power and signal.
- All leads must be wide and as short as possible especially for op amp inputs. This is in order to decrease parasitic capacitance and inductance.

- Use small resistor values to decrease time constant with parasitic capacitance. Be aware on TSH10 device of the lio error and input noise currents with high feedback resistor values.
- □ Choose component sizes as small as possible (SMD).
- On output, decrease capacitor load so as to avoid circuit stability being degraded which may cause oscillation. You can also add a serial resistor in order to minimise its influence.
- □ One can add in parallel with feedback resistor a few pF ceramic capacitor C<sub>F</sub> adjusted to optimize the settling time.

#### PACKAGE MECHANICAL DATA

8 PINS - PLASTIC MICROPACKAGE (SO)



Dim.	Millimeters		Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С	0.25		0.5	0.010		0.020
c1		•	45°	(typ.)		•
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max.)					

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